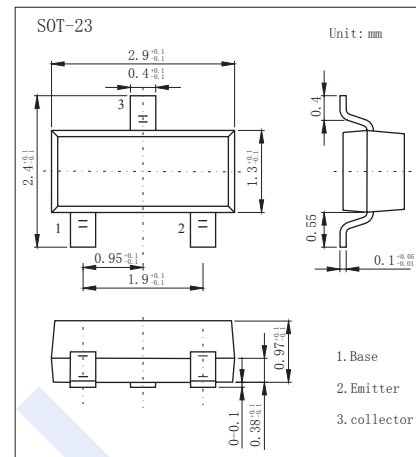


PNP Transistors

2SA1122



■ Features

- Low frequency amplifier

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

| Parameter | Symbol | Rating | Unit |
|------------------------------|-----------|-------------|------------------|
| Collector to base voltage | V_{CBO} | -55 | V |
| Collector to emitter voltage | V_{CEO} | -55 | V |
| Emitter to base voltage | V_{EBO} | -5 | V |
| Collector current | I_C | -100 | mA |
| Collector power dissipation | P_C | 150 | mW |
| Junction temperature | T_j | 150 | $^\circ\text{C}$ |
| Storage temperature | T_{stg} | -55 to +150 | $^\circ\text{C}$ |

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

| Parameter | Symbol | Test conditions | Min | Typ | Max | Unit |
|---|---------------|---|-----|-----|-------|---------------|
| Collector to base breakdown voltage | $V_{(BR)CBO}$ | $I_C = -100\mu\text{A}, I_E = 0$ | -55 | | | V |
| Collector to emitter breakdown voltage | $V_{(BR)CEO}$ | $I_C = -1\text{ mA}, R_{BE} = \infty$ | -55 | | | V |
| Emitter to base breakdown voltage | $V_{(BR)EBO}$ | $I_E = -100\mu\text{A}, I_C = 0$ | -5 | | | V |
| Collector cutoff current | I_{CBO} | $V_{CB} = -30\text{ V}, I_E = 0$ | | | -0.1 | μA |
| Emitter cutoff current | I_{EBO} | $V_{EB} = -4\text{ V}, I_C = 0$ | | | -0.1 | μA |
| DC current transfer ratio | h_{FE} | $V_{CE} = -12\text{ V}, I_C = -2\text{ mA}$ | 160 | | 800 | |
| Collector to emitter saturation voltage | $V_{CE(sat)}$ | $I_C = -10\text{ mA}, I_B = -1\text{ mA}$ | | | -0.5 | V |
| Base to emitter voltage | V_{BE} | $V_{CE} = -12\text{ V}, I_C = -2\text{ mA}$ | | | -0.75 | V |

■ h_{FE} Classification

| Marking | CC | CD | CE |
|----------|---------|---------|---------|
| h_{FE} | 160~320 | 250~500 | 400~800 |

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■ Typical Characteristics

